(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
24 July 2008 (24.07.2008)

PCT

(10) International Publication Number
WO 2008/088459 A1

(51) International Patent Classification:
H01L 21/306 (2006.01)

(21) International Application Number:
PCT/US2007/024404

(22) International Filing Date:
20 November 2007 (20.11.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/644,779 21 December 2006 (21.12.2006) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*

(54) **Title:** METHOD OF DAMAGED LOW-K DIELECTRIC FILM LAYER REMOVAL

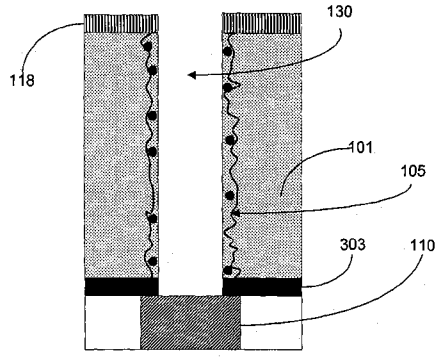


Figure 3A

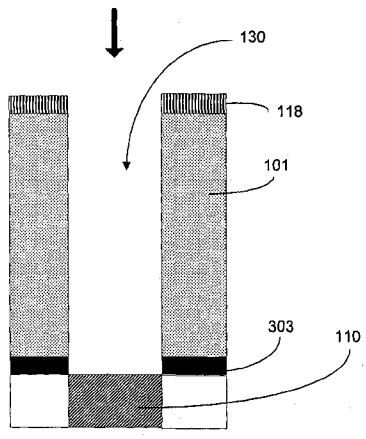


Figure 3B

(57) **Abstract:** An apparatus, system and method for removing a damaged material from a low-k dielectric film layer include identifying a control chemistry, the control chemistry configured to selectively remove the damaged material from the low-k dielectric film layer, the damaged material being in a region where a feature was formed through the low-k dielectric film layer; establishing a plurality of process parameters characterizing aspects of the damaged material to be removed and applying the control chemistry to the low-k dielectric film layer, the application of the control chemistry being defined based on the established process parameters of the damaged material, such that the damaged material is substantially removed from the areas around the feature and the areas around the feature are substantially defined by low-k characteristics of the low-k dielectric film layer.

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